

### Silicon PIN Photodiode

#### Description

BPW97 is an extra high speed PIN photodiode in a hermetically sealed TO18 package.

Unlike most similar devices, the cathode terminal is isolated from case and connected to a third terminal, giving the user all the means to improve shielding of his system.

Due to its high precision flat glass window and its accurate chip alignment, this device is recommended for ambitious applications in the optical data transmission domain.

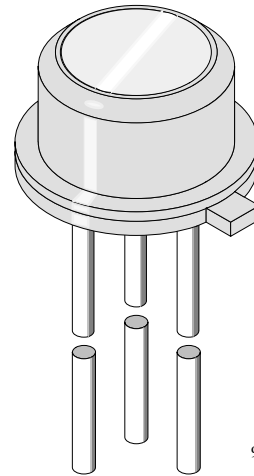
#### Features

- Extra fast response times at low operating voltages
- Exact central chip alignment
- Chip insulated
- Shielded construction
- Hermetically sealed TO-18 case
- Flat optical window
- Wide angle of half sensitivity  $\varphi = \pm 55^\circ$
- Radiant sensitive area  $A=0.25\text{mm}^2$
- Suitable for visible and near infrared radiation
- Suitable for coupling with 50  $\mu\text{m}$  gradient index fiber

#### Applications

Wide band detector for demodulation of fast signals, e.g. of lasers and GaAs emitters.

Detector for optical communication, e.g. for optical fiber transmission systems with only 5 V power supply.



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### Absolute Maximum Ratings

 $T_{amb} = 25^{\circ}\text{C}$ 

Parameter	Test Conditions	Symbol	Value	Unit
Reverse Voltage		$V_R$	60	V
Power Dissipation	$T_{amb} \leq 25^{\circ}\text{C}$	$P_V$	285	mW
Junction Temperature		$T_j$	125	$^{\circ}\text{C}$
Storage Temperature Range		$T_{stg}$	-55...+125	$^{\circ}\text{C}$
Soldering Temperature	$t \leq 5\text{ s}$	$T_{sd}$	260	$^{\circ}\text{C}$
Thermal Resistance Junction/Ambient		$R_{thJA}$	350	K/W

### Basic Characteristics

 $T_{amb} = 25^{\circ}\text{C}$ 

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	$I_F = 50\text{ mA}$	$V_F$		0.9	1.2	V
Breakdown Voltage	$I_R = 100\ \mu\text{A}, E = 0$	$V_{(BR)}$	60			V
Reverse Dark Current	$V_R = 50\text{ V}, E = 0$	$I_{ro}$		1	5	nA
Diode Capacitance	$V_R = 50\text{ V}, f = 1\text{ MHz}, E = 0$	$C_D$		1.7		pF
Dark Resistance	$V_R = 10\text{mV}, E = 0, f = 0$	$R_D$		5		$\text{G}\Omega$
Serial Resistance	$V_R = 50\text{ V}, f = 1\text{ MHz}$	$R_S$		180		$\Omega$
Reverse Light Current	$E_e = 1\text{ mW/cm}^2, \lambda = 870\text{ nm}, V_R = 50\text{ V}$	$I_{ra}$	1.0	1.3		$\mu\text{A}$
Reverse Light Current	$E_e = 1\text{ mW/cm}^2, \lambda = 950\text{ nm}, V_R = 50\text{ V}$	$I_{ra}$		0.9		$\mu\text{A}$
Temp. Coefficient of $I_{ra}$	$V_R = 50\text{ V}, \lambda = 870\text{ nm}$	$TK_{Ira}$		0.2		%/K
Absolute Spectral Sensitivity	$V_R = 5\text{ V}, \lambda = 870\text{ nm}$	$s(\lambda)$		0.50		A/W
Absolute Spectral Sensitivity	$V_R = 5\text{ V}, \lambda = 950\text{ nm}$	$s(\lambda)$		0.35		A/W
Angle of Half Sensitivity		$\varphi$		$\pm 55$		deg
Wavelength of Peak Sensitivity		$\lambda_p$		810		nm
Range of Spectral Bandwidth		$\lambda_{0.5}$		560...960		nm
Quantum Efficiency	$\lambda = 850\text{ nm}$	$\eta$		80		%
Noise Equivalent Power	$V_R = 50\text{ V}, \lambda = 870\text{ nm}$	NEP		$3.6 \times 10^{-14}$		$\text{W}/\sqrt{\text{Hz}}$
Detectivity	$V_R = 50\text{ V}, \lambda = 870\text{ nm}$	$D^*$		$1.4 \times 10^{12}$		$\text{cm}\sqrt{\text{Hz}}/\text{W}$
Rise Time	$V_R = 3.8\text{ V}, R_L = 50\Omega, \lambda = 780\text{ nm}$	$t_r$		1.2		ns
Fall Time	$V_R = 3.8\text{ V}, R_L = 50\Omega, \lambda = 780\text{ nm}$	$t_f$		1.2		ns
Rise Time	$V_R = 50\text{ V}, R_L = 50\Omega, \lambda = 820\text{ nm}$	$t_r$		0.6		ns
Fall Time	$V_R = 50\text{ V}, R_L = 50\Omega, \lambda = 820\text{ nm}$	$t_f$		0.6		ns
Cut-Off Frequency	$\lambda = 820\text{ nm}$	$f_c$		1		GHz

## Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

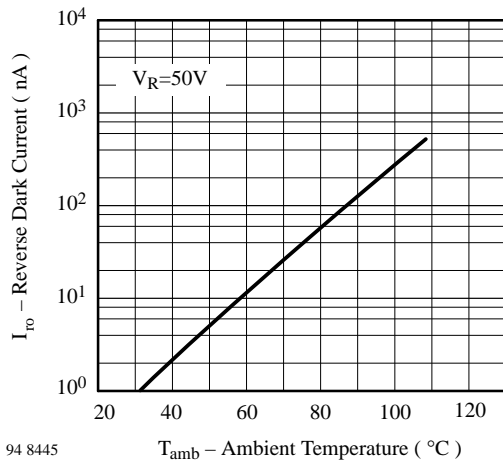


Figure 1 : Reverse Dark Current vs. Ambient Temperature

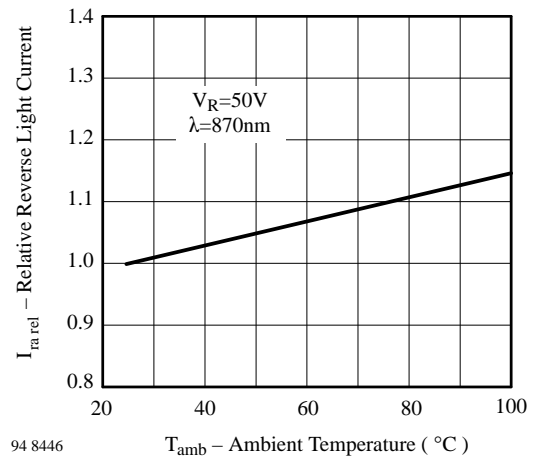


Figure 2 : Relative Reverse Light Current vs. Ambient Temperature

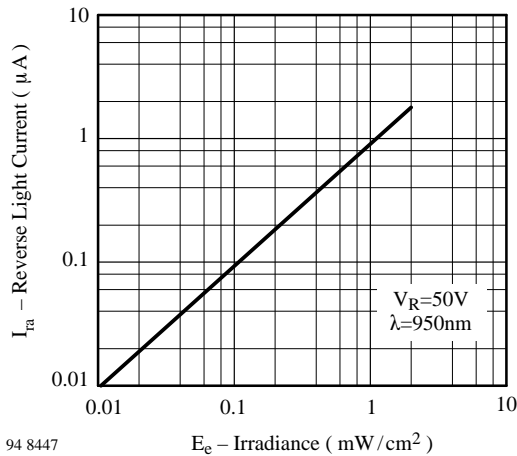


Figure 3 : Reverse Light Current vs. Irradiance

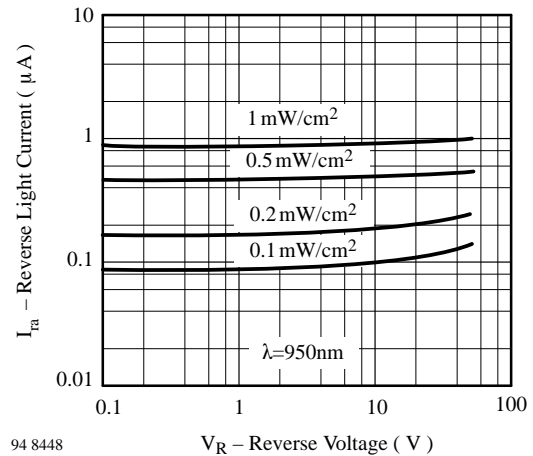


Figure 4 : Reverse Light Current vs. Reverse Voltage

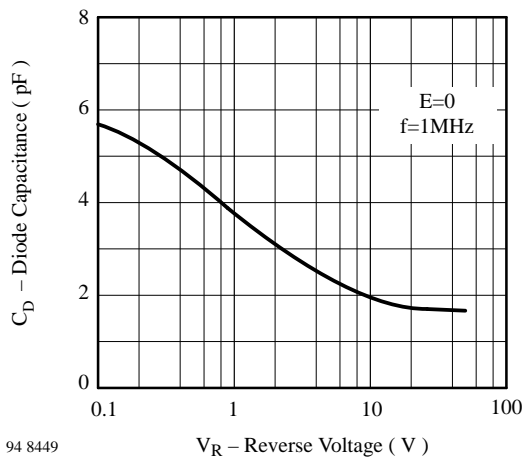


Figure 5 : Diode Capacitance vs. Reverse Voltage

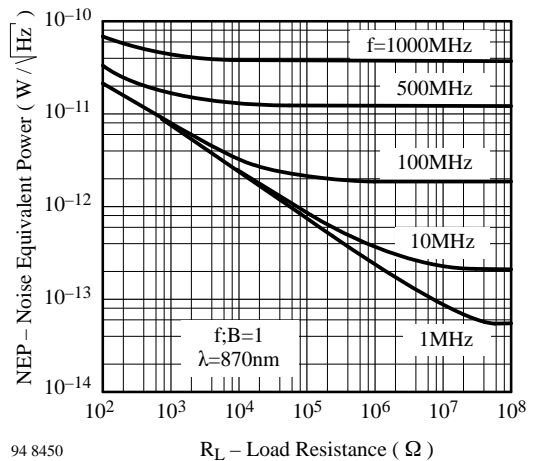
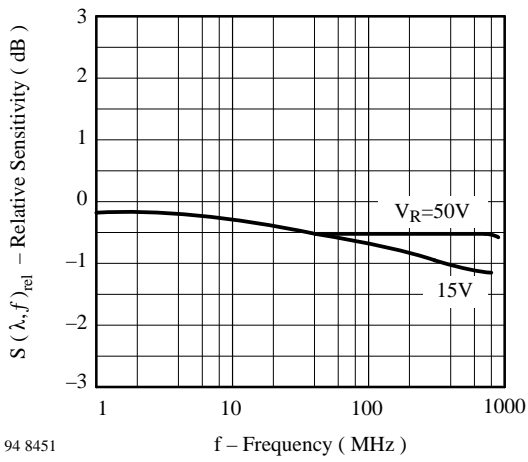
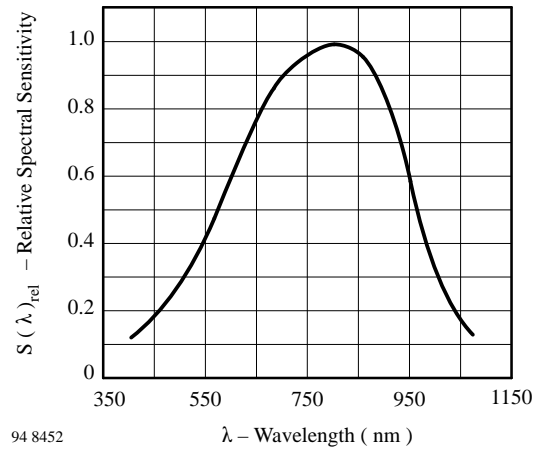


Figure 6 : Noise Equivalent Power vs. Load Resistance



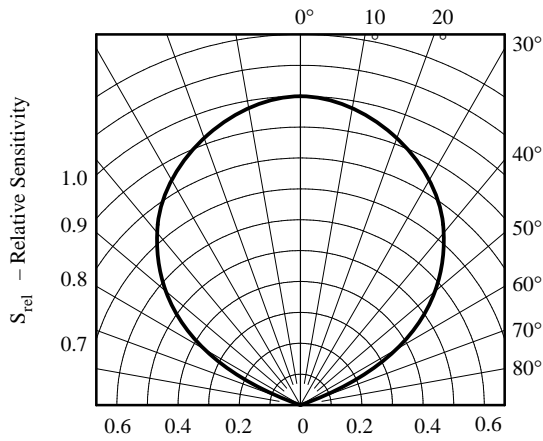
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Figure 7 : Relative Sensitivity vs. Frequency



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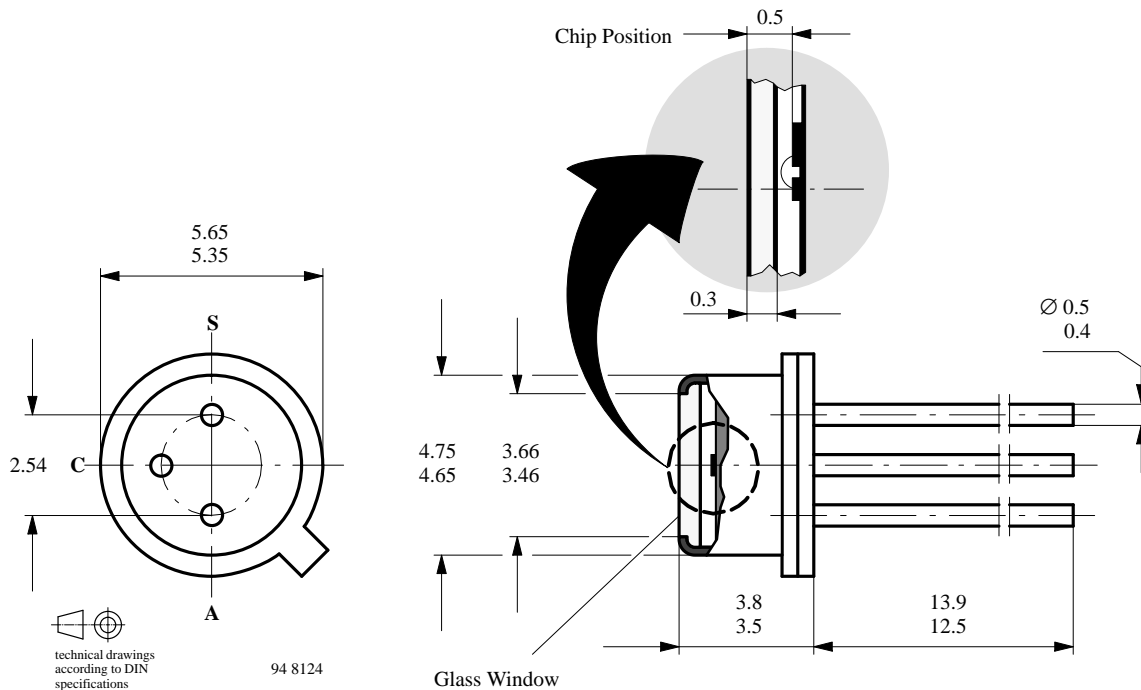
Figure 8 : Relative Spectral Sensitivity vs. Wavelength



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Figure 9 : Relative Radiant Sensitivity vs. Angular Displacement

## Dimensions in mm



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